

METHOD FOR FORMING A LOW RESISTANCE MAGNETIC TUNNEL JUNCTION STRUCTURE

ABSTRACT

5 The present disclosure describes methods for forming magnetic tunnel junction
(MTJ) devices involving the use of diffusion components selected to alter the device
properties. The magnetic tunnel junction structure is formed through diffusion
components migrating from one layer of the MTJ structure to the tunneling barrier layer.
Incorporation of the migrated components at the barrier layer adjusts the properties of the
10 MTJ device.